

SEP8736

AlGaAs Infrared Emitting Diode

FEATURES

- Side-looking plastic package
- 10° (nominal) beam angle
- 880 nm wavelength
- Enhanced coupling distance
- Mechanically and spectrally matched to SDP8436 phototransistor



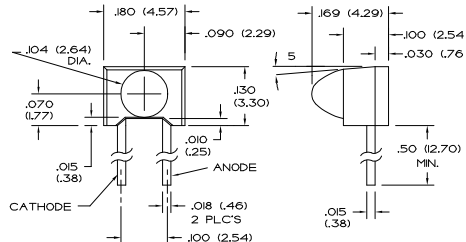
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DESCRIPTION

The SEP8736 is an aluminum gallium arsenide infrared emitting diode molded in a side-emitting smoke gray plastic package. The body and integral lens design combines the mounting advantage of a side-emitting package with the narrow emission pattern of a T-1 style device. The SEP8736 IRED is designed for those applications which require longer coupling distances than standard side-emitting devices can provide, such as touch screens. The IRED is also especially well suited to applications in which adjacent channel crosstalk could be a problem.

OUTLINE DIMENSIONS in inches (mm)

Tolerance	3 plc decimals	±0.005(0.12)
	2 plc decimals	±0.020(0.51)



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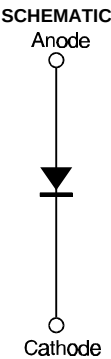
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ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)						
PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Irradiance ⁽¹⁾	H				mW/cm ²	I _F =20 mA
SEP8736-001		0.5				
SEP8736-002		1.2		3.0		
SEP8736-003		1.7				
Forward Voltage	V _F			1.7	V	I _F =20 mA
Reverse Breakdown Voltage	V _{BR}	3.0			V	I _R =10 μA
Peak Output Wavelength	λ _p		880		nm	
Spectral Bandwidth	Δλ		80		nm	
Spectral Shift With Temperature	Δλ _p /ΔT		0.2		nm/°C	
Beam Angle ⁽²⁾	Ø		10		degr.	I _F =Constant
Radiation Rise And Fall Time	t _r , t _f		0.7		μs	

- Notes
- Measured in mW/cm² into a 0.104 (2.64) diameter aperture placed 0.500(12.7) from the lens tip.
 - Beam angle is defined as the total included angle between the half intensity points.

- ABSOLUTE MAXIMUM RATINGS**
(25°C Free-Air Temperature unless otherwise noted)
- Continuous Forward Current 50 mA
 - Power Dissipation 100 mW ⁽¹⁾
 - Operating Temperature Range -40°C to 85°C
 - Storage Temperature Range -40°C to 85°C
 - Soldering Temperature (5 sec) 240°C

- Notes
- Derate linearly from 25°C free-air temperature at the rate of 0.78 mW/°C.



Honeywell reserves the right to make changes in order to improve design and supply the best products possible.

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Fig. 1 Radiant Intensity vs Angular Displacement

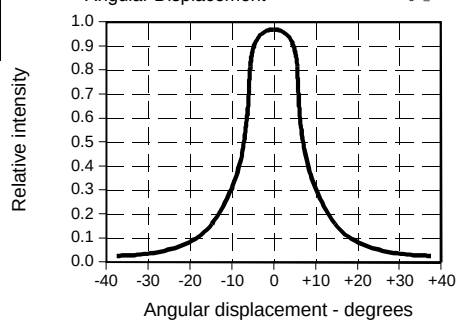


Fig. 2 Radiant Intensity vs Forward Current

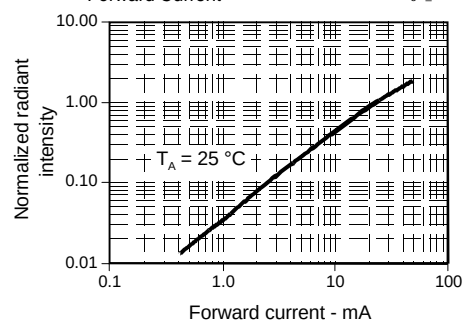


Fig. 3 Forward Voltage vs Forward Current

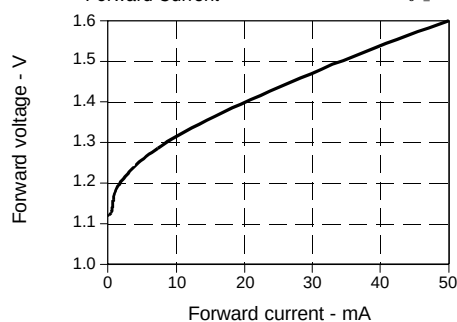


Fig. 4 Forward Voltage vs Temperature

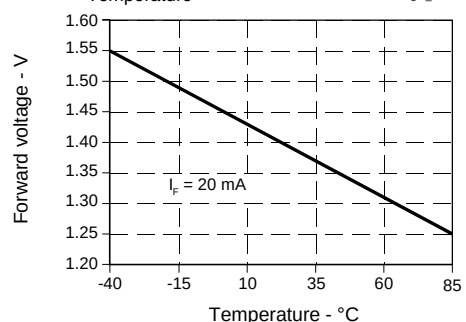


Fig. 5 Spectral Bandwidth

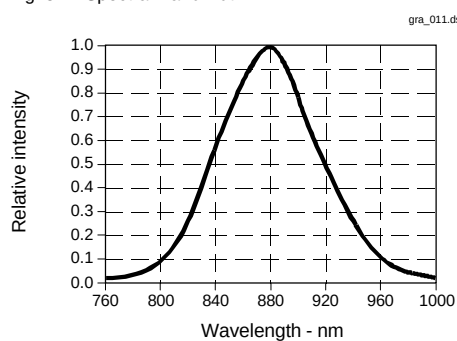
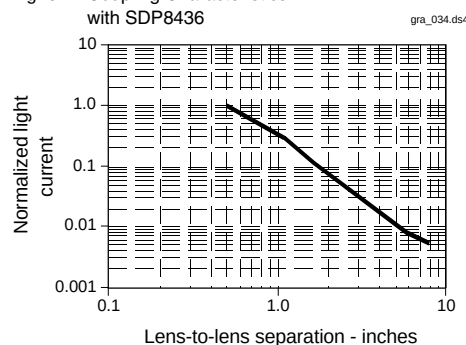


Fig. 6 Coupling Characteristics with SDP8436

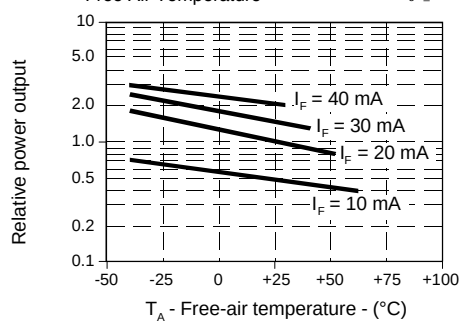


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Fig. 7 Relative Power Output vs
Free Air Temperature

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All Performance Curves Show Typical Values